

CLAIMS

1-7. (Cancelled)

8. (Previously Presented) A method for treating a working surface of a quartz semiconductor manufacturing substrate comprising:

preparing a quartz semiconductor manufacturing substrate to provide a working surface having an initial working surface roughness;

ultrasonically acid-etching said working surface to increase said initial working surface roughness of said working surface by at least about 10%; and

grit blasting said working surface after ultrasonically acid-etching said working surface with a fine grit having a mesh size greater than about 100.

9. (Previously Presented) A method for treating said working surface of said quartz semiconductor manufacturing substrate as recited in claim 8 wherein said fine grit has a mesh size greater than about 200.

10. (Previously Presented) A method for treating said working surface of said quartz semiconductor manufacturing substrate as recited in claim 8 wherein said acid-etching is a first acid-etching and further comprising a second acid-etching of said working surface after fine grit blasting said working surface.

11. (Previously Presented) A method for treating said working surface of said quartz semiconductor manufacturing substrate as recited in claim 10 wherein said

first acid-etching removes substantially more material from said working surface than said second acid-etching.

12-45. (Cancelled)